Digital transistors (built-in resistor)

DTC323TU / DTC323TK / DTC323TS

Features

In addition to the features of regular digital transistors,

- 1) Low VcE(sat) makes these transistors ideal for muting circuits. (Typ. 0.04V at lc/lb=50/2.5mA)
- 2) They can be used at high current. (IcMax. =600mA)

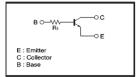
●Absolute maximum ratings (Ta=25°C)

| Pa | Symbol | Limits | Unit | | |
|---------------------------|---------------------|----------|------|----|--|
| Collector-base voltage | | Vсво | 30 | v | |
| Collector-emitter voltage | | VCEO | 15 | V | |
| Emitter-base voltage | | Vebo | 5 | V | |
| Collector current | | lc | 600 | mA | |
| Collector power | DTC323TU / DTC323TK | Pc | 200 | mW | |
| dissipation | DTC323TS | PC | 300 | | |
| Junction temperature | | Tj | 150 | °C | |
| Storage temperat | Tstg | -55~+150 | °C | | |

Package, marking, and packaging specifications

| Part No. | DTC323TU | DTC323TK | DTC323TS |
|------------------------------|----------|----------|----------|
| Package | UMT3 | SMT3 | SPT |
| Marking | H02 | H02 | — |
| Packaging code | T106 | T146 | TP |
| Basic ordering unit (pieces) | 3000 | 3000 | 5000 |

Circuit schematic



●Electrical characteristics (Ta=25℃)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions | |
|--------------------------------------|----------|------|------|------|------|--------------------------------------|--|
| Collector-base breakdown voltage | ВУсво | 30 | — | — | V | Ic=50 μA | |
| Collector-emitter breakdown voltage | BVCEO | 15 | — | — | V | Ic=1mA | |
| Emitter-base breakdown voltage | BVEBO | 5 | — | — | V | Iε=50 μ A | |
| Collector cutoff current | Ісво | - | — | 0.5 | μA | Vcb=20V | |
| Emitter cutoff current | Іево | - | — | 0.5 | μA | VEB=4V | |
| Collector-emitter saturation voltage | VCE(sat) | - | 40 | 80 | mV | Ic/Is=50mA/2.5mA | |
| DC current transfer ratio | hfe | 100 | 250 | 600 | - | Ic=50mA, VcE=5V | |
| Input resistance | B1 | 1.64 | 2.2 | 2.86 | kΩ | _ | |
| Transition frequency | fr | — | 200 | — | MHz | Vce=10V, le=-50mA, f=100MHz * | |
| Output on resistance | Ron | - | 0.65 | — | Ω | $V_1=7V$, $R_L=1k\Omega$, $f=1kHz$ | |

(96-348-C323T)

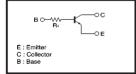
Digital transistors (built-in resistor)

Features

In addition to the features of regular digital transistors,

- 1) Low VCE(sat) makes these transistors ideal for muting circuits.
- (Typ. 0.04V at Ic/IB=50/2.5mA)
- 2) They can be used at high current. (ICMax. =600mA)

Circuit schematic



●Absolute maximum ratings (Ta=25℃)

| Parameter | | Symbol | Limits | Unit | |
|---------------------------|----------|--------|----------|------|--|
| Collector-base voltage | | Vсво | 30 | V | |
| Collector-emitter voltage | | VCEO | 15 | V | |
| Emitter-base voltage | | VEBO | 5 | V | |
| Collector current | | lc | 600 | mA | |
| Collector power | DTC343TK | Pc | 200 | mW | |
| dissipation | DTC343TS | | 300 | | |
| Junction temperature | | Tj | 150 | °C | |
| Storage temperature | | Tstg | -55~+150 | ĉ | |

Package, marking, and packaging specifications

| Part No. | DTC343TK | DTC343TS | |
|------------------------------|----------|----------|--|
| Package | SMT3 | SPT | |
| Marking | H03 | — | |
| Packaging code | T146 | TP | |
| Basic ordering unit (pieces) | 3000 | 5000 | |

Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|--------------------------------------|----------|------|------|------|------|------------------------------------|
| Collector-base breakdown voltage | ВУсво | 30 | — | — | V | Ic=50 µ A |
| Collector-emitter breakdown voltage | BVCEO | 15 | — | — | V | Ic=1mA |
| Emitter-base breakdown voltage | BVEBO | 5 | — | — | V | IE=50 μ A |
| Collector cutoff current | Ісво | — | — | 0.5 | μA | Vcs=20V |
| Emitter cutoff current | Ієво | — | — | 0.5 | μA | VEB=4V |
| Collector-emitter saturation voltage | VCE(sat) | — | 40 | 80 | mV | Ic=50mA , IB=2.5mA |
| DC current transfer ratio | hre | 100 | 250 | 600 | — | Ic=50mA, Vce=5V |
| Input resistance | R1 | 3.29 | 4.7 | 6.11 | kΩ | _ |
| Transition frequency | fт | - | 200 | — | MHz | Vce=10V, le=-50mA, f=100MHz * |
| Output on resistance | Ron | - | 0.95 | - | Ω | $V_1=7V$, $R=1k\Omega$, $f=1kHz$ |

* Transition frequency of the device.



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